PATENT ASSIGNMENT

Electronic Version v1.1
Stylesheet Version v1.1

SUBMISSION TYPE: NEW ASSIGNMENT

NATURE OF CONVEYANCE: ASSIGNMENT

CONVEYING PARTY DATA

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<td>Street Address</td>
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<td>Internal Address</td>
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<td>City</td>
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<tr>
<td>State/Country</td>
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CORRESPONDENCE DATA

Fax Number: (408)801-8512

Correspondence will be sent via US Mail when the fax attempt is unsuccessful.

Phone: 4088012863

Email: simona.benjamin@sandisk.com

Correspondent Name: SanDisk Corporation

Address Line 1: 601 Mccarthy Boulevard

Address Line 2: Patent Department/Simona Benjamin

Address Line 4: Milpitas, CALIFORNIA 95035

ATTORNEY DOCKET NUMBER: SDK0679.001US

NAME OF SUBMITTER: Simona Benjamin

Total Attachments: 5

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PATENT
REEL: 026369 FRAME: 0044
ASSIGNMENT

WHEREAS, SanDisk Corporation, a Delaware corporation, doing business at 601 McCarthy Boulevard, Milpitas, CA 95035 (hereinafter referred to as ASSIGNOR), holds right, title and interest throughout the world in and to the patents and patent applications set forth in the attached Exhibit A, together with all divisions, continuations, or continuations-in-part thereof, and all patents issuing thereon including reissues, renewals, substitutions, re-examinations and extensions thereof, and any and all corresponding foreign patents and patent applications (hereinafter referred to as, collectively, THE ASSIGNED PATENT RIGHTS);

WHEREAS, SanDisk Technologies Inc., a Texas corporation, doing business at Two Legacy Town Center, 6900 North Dallas Parkway, Plano, Texas 75024, (hereinafter referred to as ASSIGNEE), is desirous of acquiring the full and exclusive right, title and interest in the Assigned Patent Rights;

NOW, THEREFORE, for good and valuable consideration, the receipt of which is hereby acknowledged, ASSIGNOR hereby assigns, transfers and conveys unto the said ASSIGNEE, and ASSIGNEE accepts, all of ASSIGNOR’s right, title and interest throughout the world in and to THE ASSIGNED PATENT RIGHTS and to all Letters Patent or applications or similar legal protection, not only in the United States and its territorial possessions, but in all countries foreign thereto to be obtained for THE ASSIGNED PATENT RIGHTS, and to any continuation, division, renewal, substitute or reissue thereof or any legal equivalent thereof in the United States or a foreign country for the full term or terms for which the same may be granted, including all priority rights under the International Convention; and ASSIGNOR hereby authorizes and requests the United States Commissioner of Patents and Trademarks and any officials of foreign countries whose duty it is to issue patents on applications as aforesaid, to issue all patents for THE ASSIGNED PATENT RIGHTS to ASSIGNEE in accordance with the terms of this ASSIGNMENT but subject to reserved rights including but not limited to those previously retained by, granted to, or owned by, the United States government, educational institutions or both and hereby transfers and conveys all rights of action, power and benefit belonging to or accruing from THE ASSIGNED PATENT RIGHTS including the right to undertake proceedings to recover past and future damages and claim all other relief in respect of any acts of infringement thereof whether such acts shall have been committed before or after the date of this assignment.
No other rights, immunities, or licenses, including, without limitation, any rights to any
intellectual property owned, controlled or licensable by ASSIGNOR are granted or assigned to
ASSIGNEE under this ASSIGNMENT, either expressly or by implication, estoppel, or otherwise,
other than the rights expressly recited herein.

ASSIGNOR hereby covenants that no assignment, sale, agreement or encumbrance
has been or will be made or entered into which would knowingly conflict with this Agreement;

ASSIGNOR further covenants that ASSIGNEE will, upon its lawful request, reasonably
be provided with all pertinent facts and documents relating to THE ASSIGNED PATENT RIGHTS and
legal equivalents as may be known and reasonably accessible to ASSIGNOR and that
ASSIGNOR will testify as to the same in any administrative contest or litigation related thereto
and will promptly execute and deliver to ASSIGNEE or its legal representative any and all
papers, instruments or affidavits required to apply for, obtain, maintain, issue and enforce THE
ASSIGNED PATENT RIGHTS and said equivalents in the United States or in any foreign country,
which may be necessary or desirable to carry out the purposes thereof.
IN TESTIMONY WHEREOF, I hereunto set my hand as of the date indicated below.

SANDISK CORPORATION

Dated: 4th April 2011

Name: Andy Bruner
Title: EVP and CFO

STATE OF California )
COUNTY OF Santa Clara ) ss.

On this 4th day of April, 2011, before me Arevil Branner Waters, Notary Public, the undersigned Notary Public, personally appeared Andy Bruner, who proved to me on the basis of satisfactory evidence to be the person(s) whose name(s) is/are subscribed to the within instrument and acknowledged to me that he/she/they executed the same in his/her/their authorized capacity(ies), and that by his/her/their signature(s) on the instrument the person(s), or the entity upon behalf of which the person(s) acted, executed the instrument.

I certify under PENALTY OF PERJURY under the laws of the State of California that the foregoing paragraph is true and correct.

WITNESS my hand and official seal.

Signature: ____________________________
Signature of Notary Public

We accept the Assignment

SANDISK TECHNOLOGIES INC.

Dated: 4/4/11

Name: James F. Breisford
Title: President and Secretary

STATE OF California )
COUNTY OF Santa Clara ) ss.

On this 4th day of April, 2011, before me L. Benjamin, Notary Public, the undersigned Notary Public, personally appeared James F. Breisford, who proved to me on the basis of satisfactory evidence to be the person(s) whose name(s) is/are subscribed to the within instrument and acknowledged to me that he/she/they executed the same in his/her/their authorized capacity(ies), and that by his/her/their signature(s) on the instrument the person(s), or the entity upon behalf of which the person(s) acted, executed the instrument.

I certify under PENALTY OF PERJURY under the laws of the State of California that the foregoing paragraph is true and correct.

WITNESS my hand and official seal.

Signature: ____________________________
Signature of Notary Public
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<th>INVENTORS</th>
<th>TITLE</th>
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